5 é / Descriptions

9 5 : .> / / x 4 6 4 ! - } â ’ož Silicon NPN transistor in a SOT-89 Plastic Package.

¤ ª / Features

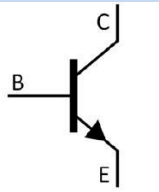
: ; m k —)í D }ož

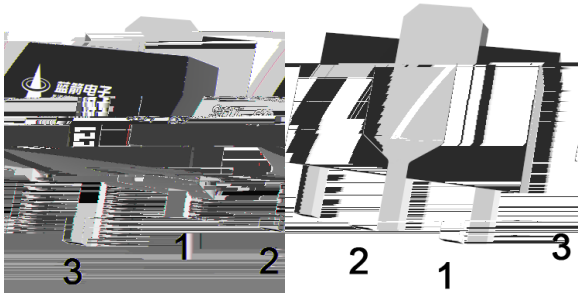
Complementary pair with 8550T, HF Product.

9 ä y Ý èož

Power amplifier applications.

Ã W] Ô · / Equivalent Circuit





PIN1 y Base PIN 2 y Collector PIN 3 y Emitter

, M V / Marking

h_{FE} Classifications Symbol	B	C	D
h_{FE} Range	85 160	120 200	160 300
Marking	HY1B	HY1C	HY1D

@ *f* Parameter	… Z Symbol	*f* › Rating	% y Unit
Collector to Base Voltage	V_{CBO}	40	V
Collector to Emitter Voltage	V_{CEO}	25	V
Emitter to Base Voltage	V_{EBO}	6.0	V
Collector Current - Continuous	I_C	1.5	A
Collector Base - Continuous	I_B	0.5	A
Collector Power Dissipation	P_C	500	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T		

Ô ? d • Ž ¢ / Electrical Characteristic Curve

Ø ¤ =) ¢ / Package Dimensions

, M y ƒ / Marking Instructions

HY1B

ª ¢ y

. y ¸ [W A

? y º Z W A

(y N, + ã W A

y ÿ D Z W A k š ÿ D Z J

Note:

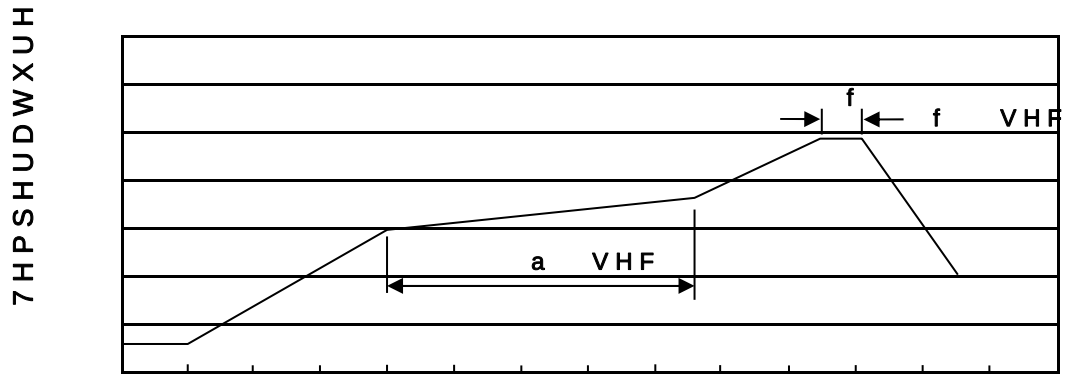
H: Company Code

Y1: Product Type

B y h_{FE} Classifications Symbol

**: Lot No. Code, code change with Lot No

š WD t ... • Ž ¢ (x /) / : K S V K X G Z [X K 6 X U L O R K L U X / 8 8 K L R U] 9 U R J K X O T M 6



7 L P H V H F

ª ¢ y

Note:

1o• Ä ½ “ † 150 ½180 - k ž • 60 ½90sec;

1.Preheating:150~180 - , Time:60~90sec.

2o• Q › “ † 245 r5 - k ž • 4 Ò 5 r0.5sec;

2.Peak Temp.:245 r5 - , Duration:5 r0.5sec.

3o•D N ò i Ò 0 , † 2 ½10 - /sec.

3. Cooling Speed: 2~10 - /sec.

ÂD /Cã p ¯ »] / Resistance to Soldering Heat Test Conditions

“ † y 260 r5 - ž • y 10 r1 sec. Temp.:260±5 Time:10±1 sec

G P á / Packaging SPEC.

2 & x / REEL

Package Type 7>û ˜ E	Units ;>û ¦H					Dimension ;>û p . (unit Æmm³)		
	Units/Reel / --	Reels/Inner Box -- /-	Units/Inner Box /-	Inner Boxes/Outer Box - /1ç	Units/Outer Box /1ç	Reel	Inner Box×	Outer Box1ç
SOT-89	1,000	7	7,000	6	42,000	7 s ×12	180×120×180	390×385×205

„ Ð y ƒ / Notices